



IBT42N

15 MHz – 4.2 GHz HIGH POWER BIAS-T

REV B
July 2015

Key Features



- Wide Band, 15 MHz ~ 4.2 GHz
- Low Insertion Loss, 0.30 dB Typ.
- 1.2:1 VSWR
- 600 mA DC Current Handling
- 20 W CW Power Handling
- Precision Machined Housing
- Single DC Power Supply
- Meet MIL-STD-202g

Applications

- Up to 4.2 GHz Band
- Satellite Communications
- Broadcast
- RF Bench Tests
- Mobile Base Station



Absolute Maximum Ratings

Parameters	Units	Ratings
DC Voltage	V	50
DC Current	mA	600
Input Power, CW	W	20
Storage Temperature	°C	-40 ~ +85
Operating Temperature	°C	-40 ~ +85

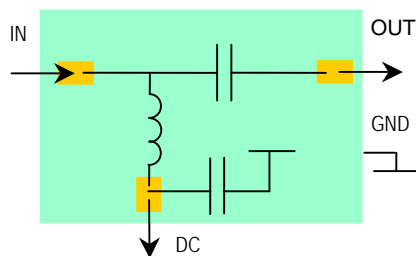
Note: Heat sink is required for high power applications!

Specifications

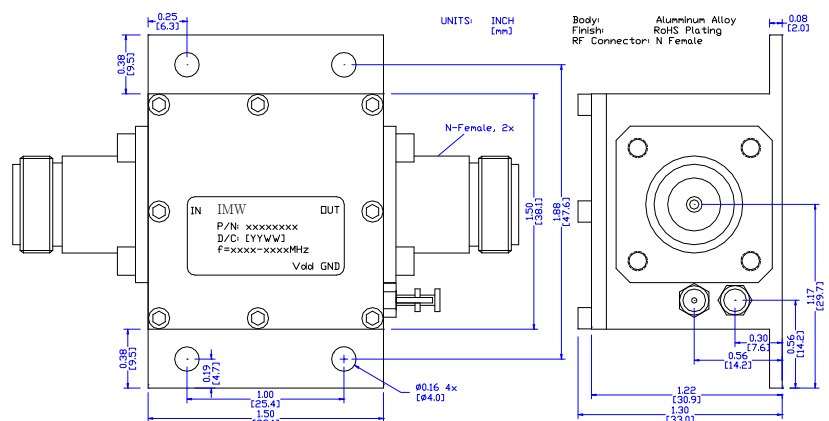
Summary of the key electrical specifications at 25°C

Index	Testing Item	Symbol	Test Constraints	Min	Typ	Max	Unit
1	Frequency Range	BW	50 Ohm Impedance	0.015		4.2	GHz
2	Insertion Loss	S_{21}	0.015 – 4.2 GHz		0.3	0.86	dB
3	VSWR	SWR_i	0.015 – 4.2 GHz		1.2:1	1.5:1	Ratio
4	Isolation, RF to DC Port		0.015 – 4.2 GHz		45		dB
5	Maximum Power Handling	P_{MAX}	0.015 – 4.2 GHz, CW			20	W
6	Maximum DC Voltage	V_{DCMAX}				50	V
7	Maximum DC Current	I_{DCMAX}				600	mA
8	Operating Temperature	T_o		-40		+85	°C

Functional Block Diagram



Outline, IP-2 Housing



Ordering Information

Model Number	Connectors	
	IN	OUT
IBT42N	N Female	N Female

Specifications and information are subject to change without notice.



Typical Data

